

AMENDMENTS TO CLAIMS

Listing Of Claims

July 11
Claims 1-33 (Canceled)

34. (Currently amended) A method for fabricating an interconnect for a ~~semiconductor component having~~ engaging a bumped contact on a semiconductor component comprising:
~~providing a substrate;~~
~~having a surface and an opposing surface;~~
~~forming a plurality of leads on the substrate surface configured to electrically engage and support the bumped contact;~~
~~and a connecting segment on the surface configured to electrically connect the leads to one another;~~
~~forming a recess in the surface substrate such that the leads cantilever over the recess and are configured for movement within the recess during electrical engagement of the bumped contact; and~~
~~forming an outer layer on each lead configured to provide a non-bonding surface for the bumped contact.~~
~~forming a conductive via in the substrate in electrical communication with the connecting segment; and~~
~~forming a contact on the opposing surface in electrical communication with the conductive via.~~

35. (Currently amended) The method of claim 34 wherein the outer layer comprises a material selected from the group consisting of Ti, TiSi₂, Al and a conductive polymer.

~~forming the conductive via step comprises forming an opening through the connecting segment and the substrate and forming a conductive material in the opening.~~

Claims 36-37 (Withdrawn)

38. (Currently amended) The method of claim 34 further comprising forming at least one blade ~~on the leads on each lead~~ configured to penetrate the bumped contact.

39. (Currently amended) A method for fabricating an interconnect for a ~~semiconductor component having~~ engaging a bumped contact on a semiconductor component comprising:

providing a substrate;
having a surface and an opposing surface;
forming a metal layer on the substrate;
forming a plurality of blades in the metal layer
configured to penetrate the bumped contact;
forming an outer layer on the metal layer configured
to provide a non-bonding surface for the bumped contact;

forming a plurality of leads on the surface in the
metal layer configured to electrically engage and support
the bumped contact, each lead including at least one blade;
and

and a connecting segment on the surface configured to
electrically connect the leads to one another;

forming a recess in the surface substrate such that
the leads are cantilevered over the recess and are
configured to move within the recess during electrical
engagement of the bumped contact.

+

forming an opening through the substrate and the
connecting segment;
forming a conductive material in the opening; and
forming a contact on the opposing surface in
electrical communication with the conductive material.

40. (Currently amended) The method of claim 39 wherein the outer layer comprises a conductive polymer.
forming the opening step comprises laser machining.

41. (Currently amended) The method of claim 39 wherein the outer layer comprises a material selected from the group consisting of a carbon film and a metal filled silicone.

~~recess is generally square having four sides and the leads extend generally orthogonally to the four sides.~~

Claim 42 (Withdrawn)

C1 cont

43. (Currently amended) The method of claim 39 further comprising forming a connecting segment on the substrate electrically connecting the leads, a conductive via in the substrate in electrical communication with the connecting segment and a contact on the substrate in electrical communication with the conductive via.

~~plurality of blades on the leads configured to penetrate the bumped contact.~~

Claims 44-48 (Withdrawn)

49. (Currently amended) A method for fabricating an interconnect for a semiconductor component having a engaging bumped contacts on a semiconductor component comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of interconnect contacts on the substrate configured to electrically engage the bumped contacts, each interconnect contact comprising a recess in the surface and a plurality of leads cantilevered over the recess configured to support a bumped contact for movement in the recess; and

forming an outer layer on each lead configured to provide non-bonding surfaces for the bumped contacts.

forming a plurality of conductive vias in the substrate in electrical communication with the interconnect contacts; and

forming a plurality of contacts on the opposing surface having a different pitch than that of the interconnect contacts.

50. (Currently amended) The method of claim 49 wherein the outer layer comprises a conductive polymer.
contacts comprise pads.

E1 Search

51. (Currently amended) The method of claim 49 further comprising forming a plurality of at least one blade ~~s~~ on the each lead ~~s~~ configured to penetrate the a bumped contact.

52-58. (Withdrawn)